#### Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

Except below description page
 "Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

Revision. 3

MOS FET

FK8V03040L

### **Panasonic**

### FK8V03040L

#### Silicon N-channel MOSFET

For lithium-ion secondary battery protection circuit For DC-DC Converter

#### ■ Features

- Low drain-source On-state Resistance RDS(on) typ = 11 m $\Omega$  (VGS = 4.5 V)
- High-speed switching : Qg = 7.2 nC
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 3D

#### ■ Packaging

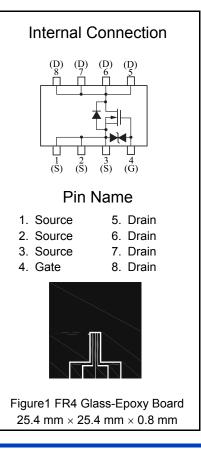
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

	Unit: mm			
2. 9				
***************************************	0.3 0.16			
	2.2.2.8			
0.65	3 4 (0.81)			
1. Source	e 5. Drain			
2. Source	e 6. Drain			
3. Source	e 7. Drain			
4. Gate	8. Drain			
Panasonic	WMini8-F1			
JEITA	SC-115			
Code	T –			

Parameter	Symbol	Rating	Unit	
Drain-source Voltage	VDS	33	V	
Gate-source Voltage	VGS	±20	V	
Drain Current (Steady State) *1	ID	10		
Drain Current (t = 10 s) *1	טו	12		
Drain Current (Pulsed) *1,*2	IDp	40	Α	
Source Current (Pulsed)	ISp	10		
(Body Diode) *1,*2	(BD)	10		
Total Power Dissipation (Steady State) *1	PD	1	W	
Total Power Dissipation (t = 10 s) *1	וט	1.5		
Channel Temperature	Tch	150	°C	
Operating Ambient Temperature	Topr	-40 to +85	°C	
Storage Temperature Range	Tstg	-55 to +150	°C	

Note) \*1 Device mounted on a glass-epoxy board (See Figure 1)

\*2 Pulse test: Ensure that the channel temperature does not exceed 150°C.



MOS FET

FK8V03040L

#### ■ Electrical Characteristics Ta = 25°C ± 3°C

#### Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	33			V
Zero Gate Voltage Drain Current	IDSS	VDS = 33 V, VGS = 0 V			10	μΑ
Gate-source Leakage Current	IGSS	VGS = $\pm 16$ V, VDS = 0 V			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = 1.12 mA, VDS = 10 V	1		2.5	V
Drain course On state Desistance	RDS(on)1	ID = 5A, VGS = 10 V		7	10	mΩ
	RDS(on)2	ID = 5A, VGS = 4.5 V		11	19	

#### **Dynamic Characteristics**

Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V	750	
Output Capacitance	Coss	f = 1 MHz	170	pF
Reverse Transfer Capacitance	Crss	1 - 1 IVII 12	100	
Turn-on Delay Time *2	td(on)	VDD = 15 V, VGS = 0 to 10 V	9	
Rise Time *2	tr	ID = 5 A	6	ns
Turn-off Delay Time *2	td(off)	VDD = 15 V, VGS = 10 to 0 V	46	115
Fall Time *2	tf	ID = 5 A	18	
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V,	7.2	
Gate-source Charge	Qgs	ID = 10 A	2.3	nC
Gate-drain Charge	Qgd	ID - 10 A	3.3	

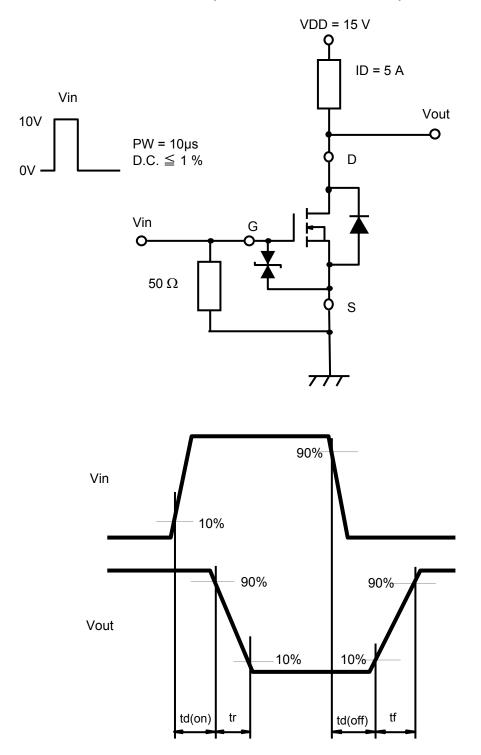
Body Diode Characteristic					
Diode Forward Voltage *1	VSD	IS = 5 A, VGS = 0 V	0.8	1.2	V

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

<sup>2. \*1</sup> Pulse test: Ensure that the channel temperature does not exceed 150°C.

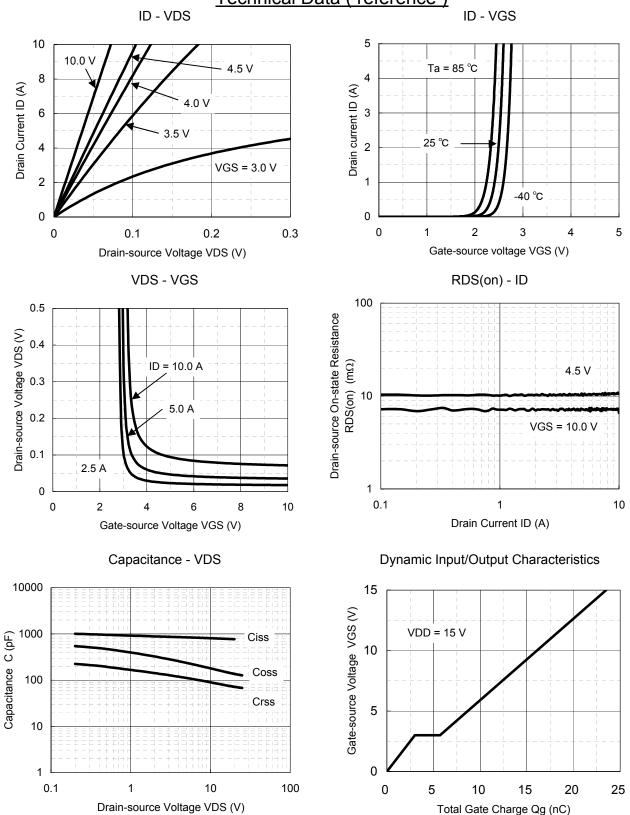
<sup>\*2</sup> Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

\*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



MOS FET FK8V03040L

### Technical Data (reference)



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2.5

2

1.5

1

0.5

0

-50

Gate-source Threshold Voltage (V)

MOS FET

## FK8V03040L

### Technical Data (reference)

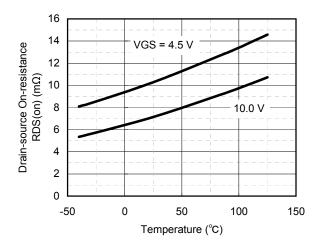
150





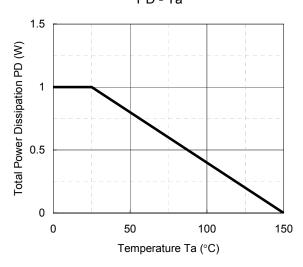
100

RDS(on) - Ta

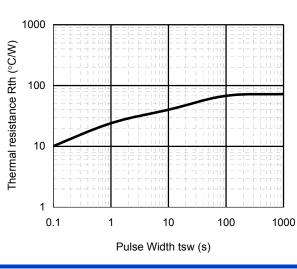


Temperature (°C)
PD - Ta

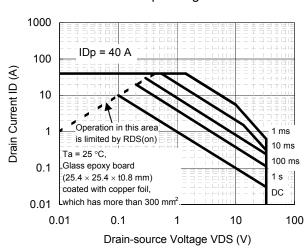
50



Rth - tsw



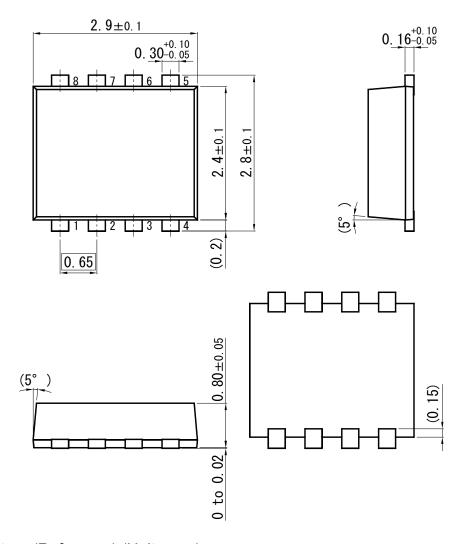
Safe Operating Area



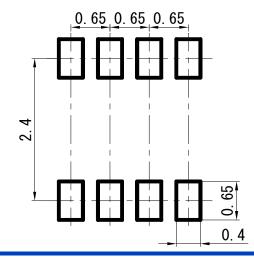
MOS FET FK8V03040L

WMini8-F1

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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